## **BCW66GLT1G**

# **General Purpose Transistor**

## **NPN Silicon**

## **Features**

• These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	45	Vdc
Collector - Base Voltage	$V_{CBO}$	75	Vdc
Emitter – Base Voltage	$V_{EBO}$	5.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	800	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

## THERMAL CHARACTERISTICS

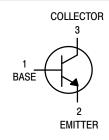
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1), T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in 99.5% alumina.



## ON Semiconductor®

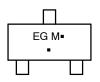
## http://onsemi.com





SOT-23 CASE 318 STYLE 6

## **MARKING DIAGRAM**



EG = Specific Device Code

M = Date Code\*

■ = Pb-Free Package (Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BCW66GLT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel
BCW66GLT3G	SOT-23 (Pb-Free)	10000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **BCW66GLT1G**

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	•	•			
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	45	_	_	Vdc
Collector – Emitter Breakdown Voltage (I <sub>C</sub> = 10 μAdc, V <sub>EB</sub> = 0)	V <sub>(BR)CES</sub>	75	_	_	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	5.0	_	_	Vdc
Collector Cutoff Current $(V_{CE} = 45 \text{ Vdc}, I_E = 0)$ $(V_{CE} = 45 \text{ Vdc}, I_E = 0, T_A = 150^{\circ}\text{C})$	- -	20 20	nAdc μAdc		
Emitter Cutoff Current (V <sub>EB</sub> = 4.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	_	20	nAdc
ON CHARACTERISTICS					
DC Current Gain $ \begin{aligned} &(I_C=100~\mu\text{Adc},V_{CE}=10~\text{Vdc})\\ &(I_C=10~\text{mAdc},V_{CE}=1.0~\text{Vdc})\\ &(I_C=100~\text{mAdc},V_{CE}=1.0~\text{Vdc})\\ &(I_C=500~\text{mAdc},V_{CE}=2.0~\text{Vdc}) \end{aligned} $	h <sub>FE</sub>	50 110 160 60	- - -	- - 400 -	-
Collector – Emitter Saturation Voltage ( $I_C = 500 \text{ mAdc}$ , $I_B = 50 \text{ mAdc}$ ) ( $I_C = 100 \text{ mAdc}$ , $I_B = 10 \text{ mAdc}$ )	V <sub>CE(sat)</sub>	_ _	- -	0.7 0.3	Vdc
Base – Emitter Saturation Voltage ( $I_C = 500$ mAdc, $I_B = 50$ mAdc)	V <sub>BE(sat)</sub>	_	_	2.0	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product (I <sub>C</sub> = 20 mAdc, V <sub>CE</sub> = 10 Vdc, f = 100 MHz)	f <sub>T</sub>	100	-	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	-	_	12	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	_	-	80	pF
Noise Figure (V <sub>CE</sub> = 5.0 Vdc, I <sub>C</sub> = 0.2 mAdc, R <sub>S</sub> = 1.0 k $\Omega$ , f = 1.0 kHz, BW = 200 Hz)	NF	-	-	10	dB
SWITCHING CHARACTERISTICS		•	•	•	•
Turn-On Time (I <sub>B1</sub> = I <sub>B2</sub> = 15 mAdc)	t <sub>on</sub>	_	-	100	ns
Turn–Off Time ( $I_C$ = 150 mAdc, $R_L$ = 150 $\Omega$ )	t <sub>off</sub>	-	_	400	ns

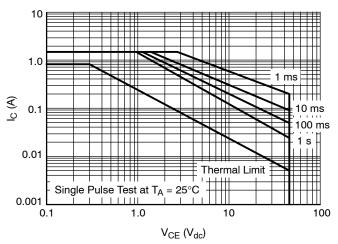
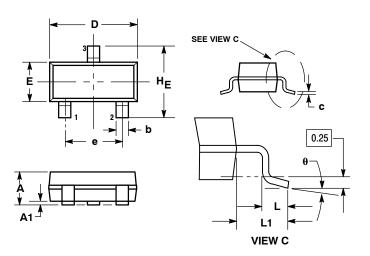


Figure 1. Safe Operating Area

### BCW66GLT1G

## PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN** 



- V112. 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 318-01 THRU -07 AND -09 OBSOLETE, NEW
- STANDARD 318-08.

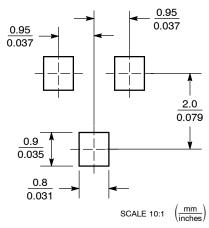
	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.89	1.00	1.11	0.035	0.040	0.044	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.37	0.44	0.50	0.015	0.018	0.020	
С	0.09	0.13	0.18	0.003	0.005	0.007	
D	2.80	2.90	3.04	0.110	0.114	0.120	
E	1.20	1.30	1.40	0.047	0.051	0.055	
е	1.78	1.90	2.04	0.070	0.075	0.081	
L	0.10	0.20	0.30	0.004	0.008	0.012	
L1	0.35	0.54	0.69	0.014	0.021	0.029	
HE	2.10	2.40	2.64	0.083	0.094	0.104	

STYLE 6:

PIN 1. BASE

- 2. 3. **EMITTER**
- COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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